

Silicon PNP Power Transistors

KSA614

DESCRIPTION

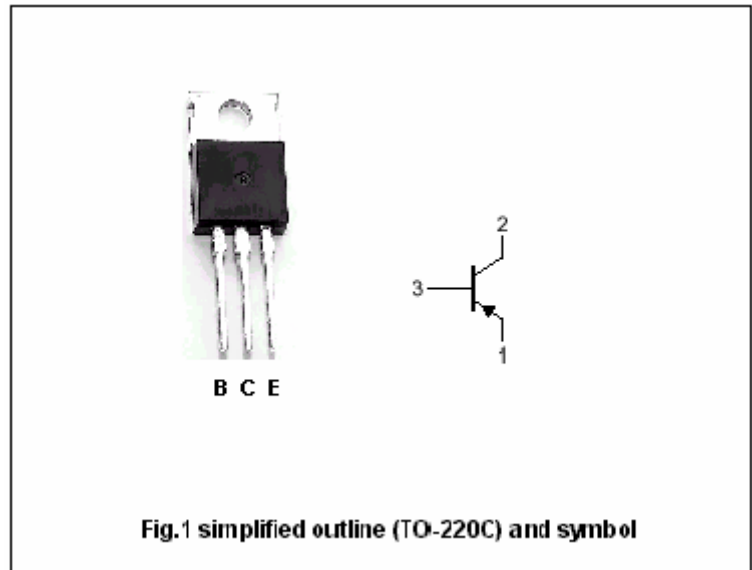
- With TO-220 package
- Collector-Base Voltage: $V_{CBO} = -80V$ (Min)
- Collector dissipation: $P_C = 25W$ @ $T_C = 25^\circ C$

APPLICATIONS

- Low frequency power amplifier
- Power regulator

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector; connected to mounting base
3	Base

Absolute maximum ratings ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-80	V
V_{CEO}	Collector-emitter voltage	Open base	-55	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current (DC)		-3	A
P_C	Collector power dissipation	$T_C = 25^\circ C$	25	W
T_j	Junction temperature		150	$^\circ C$
T_{stg}	Storage temperature		-55~150	$^\circ C$

Silicon PNP Power Transistors**KSA614****CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA ; I _B =0	-80			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-0.5mA ; I _E =0	-55			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-0.5mA ; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1A ; I _B =-0.1A			-0.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-50V ; I _E =0			-50	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-5V ; I _C =0			-50	μ A
h _{FE}	DC current gain	I _C =-0.5A ; V _{CE} =-5V	40		240	

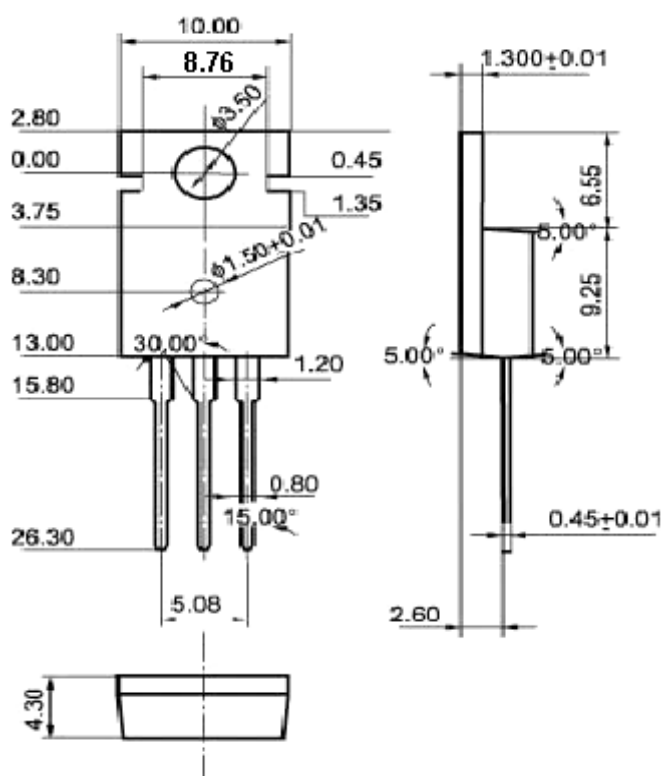
◆ **h_{FE} classifications**

R	O	Y
40-80	70-140	120-240

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PACKAGE OUTLINE

Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)

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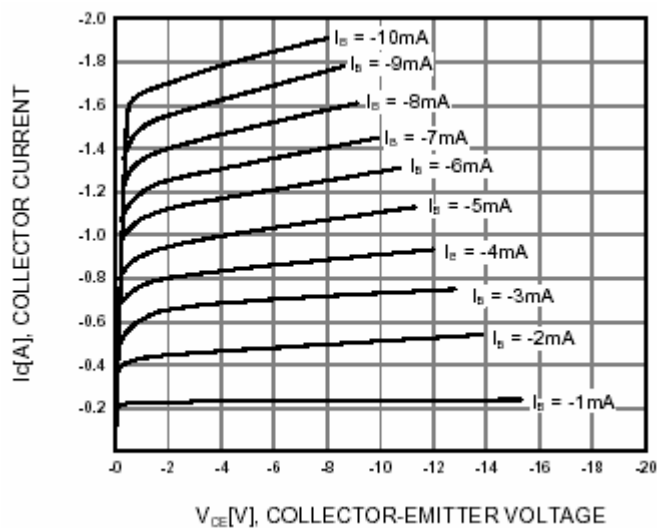


Fig.3 Static Characteristic

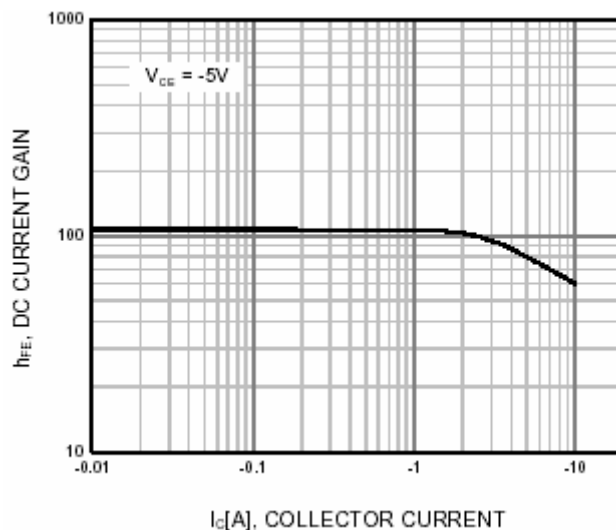


Fig.4 DC current Gain

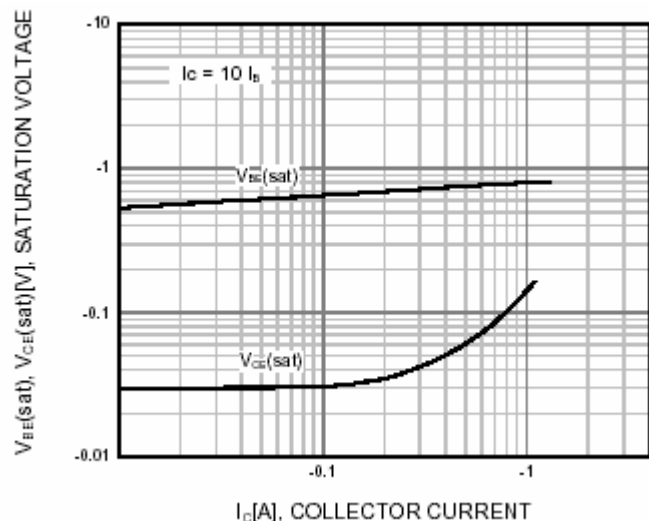
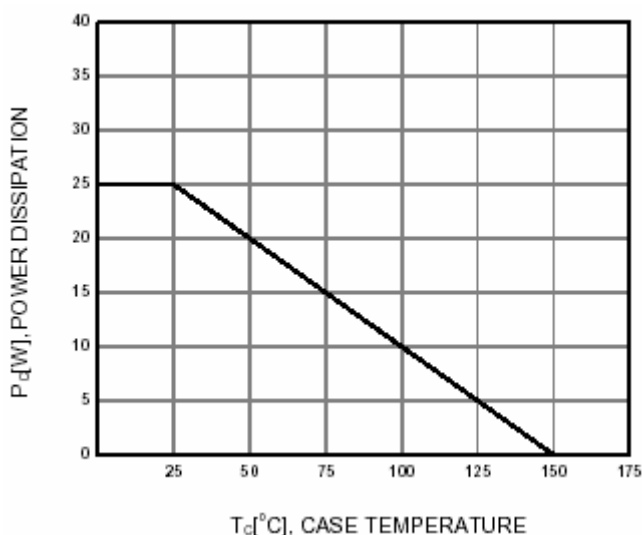
Fig.5 Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

Fig.6 Power Derating

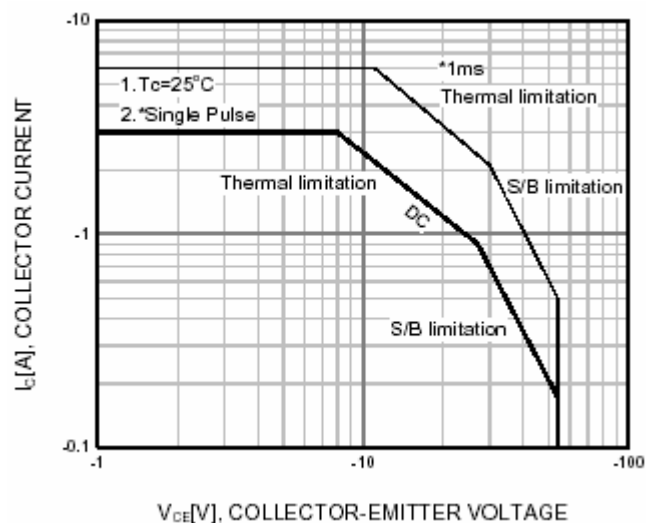


Fig.7 Safe Operating Area